EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"20030087492".pn.	US-PGPUB; USPAT	OR	OFF	2006/03/28 16:19
L4	198	438/218.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/28 16:30
L6	2473	438/199.ccls. 438/218.ccls. 438/221.ccls. 438/514.ccls. 438/739.ccls. 438/766.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/28 16:37
L7	12506	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio.sub.x n.sub.y" "sio.sub.xn.sub.y") with (strain stress tens$6 compress$6)	US-PGPUB; USPAT	OR	ON	2006/03/28 16:37
L8	216	L6 and L7	US-PGPUB; USPAT	OR	ON	2006/03/28 16:37
L9	2747	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio.sub.x n.sub.y" "sio.sub.xn.sub.y") with (strain stress tens$6 compress$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 16:52
L10	893	L9 and (etch$6 gap groove trench slot hole opening dop$6 implant$8)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 16:52
L11	95	L10 and (cmos nmos pmos nfet pfet "n-type" "p-type") and (semiconductor substrate wafer silicon)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 16:52
L12	1427	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio.sub.x n.sub.y" "sio.sub.xn.sub.y") with ((strain stress tens$6 compress$6) near (layer film))	US-PGPUB; USPAT	OR	ON	2006/03/28 16:56
L13	104	L12 same (cmos nmos pmos nfet pfet "n-type" "p-type") same (semiconductor substrate wafer silicon)	US-PGPUB; USPAT	OR	ON	2006/03/28 16:56
L14	108	L12 same (etch$6 remov$6) same (gap groove trench slot hole opening dop$6 implant$6)	US-PGPUB; USPAT	OR	ON	2006/03/28 17:04